

IN THE CLAIMS

Please amend the following claims.

1. (Currently Amended) A method of forming a dielectric layer of a device, said method comprising:

~~forming~~ depositing a dielectric layer on a substrate;

generating ionized oxygen atoms in a first chamber;

flowing said ionized oxygen atoms through a conduit coupling said first chamber to a second chamber, wherein said ionized atoms become electrically neutral reactive oxygen atoms before reaching said second chamber;

exposing said as deposited dielectric layer to said electrically neutral reactive oxygen atoms in said second chamber to form an electrically neutral reactive oxygen atom exposed as deposited dielectric layer and to improve the electrical performance of the as deposited dielectric layer; and

forming an electrode above said ~~active atomic species~~ electrically neutral reactive oxygen atom exposed as deposited dielectric layer.

2. (Original) The method of claim 1 wherein said dielectric is a metal oxide dielectric formed at a first temperature, and wherein said dielectric layer is exposed to said electrically neutral reactive oxygen atoms at a second temperature which is less than said first temperature.

3. (Original) The method of claim 1 wherein said dielectric layer comprises titanium oxide.

4. (Original) The method of claim 1 wherein said dielectric layer comprises a metal-oxide.

5. (Original) The method of claim 1 wherein said dielectric layer comprises a transition metal dielectric.

6. (Original) The method of claim 5 wherein said dielectric layer comprises tantalum pentaoxide (Ta_2O_5).

7. (Original) The method of claim 1 wherein said dielectric layer is exposed to said active atomic species while being heated to a temperature of less than 400°C .

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Currently Amended) A method of annealing a deposited oxide of a device, said method comprising:

locating a substrate in a first chamber, said substrate having ~~a~~ an as deposited oxide formed thereon;

generating a plasma comprising ionized oxygen atoms in a second chamber;

flowing said ionized oxygen atoms from said second chamber into said first chamber through a conduit wherein said ionized oxygen atoms become electrically neutral reactive oxygen atoms while flowing from said second chamber to said first chamber;

exposing said as deposited oxide to said electrically neutral reactive oxygen atoms to form an electrically neutral reactive oxygen atom exposed as deposited dielectric layer and to improve the electrical performance of the as deposited dielectric layer; and

forming an electrode above said ~~active atomic species~~ electrically neutral reactive oxygen atom exposed as deposited oxide layer.

15. (Currently Amended) The method of claim 14 wherein said as deposited oxide is exposed to said reactive oxygen atoms while heating said substrate to at a temperature of less than 400°C.

16. (Original) The method of claim 14 wherein said second chamber is a microwave applicator cavity of a remote plasma generator.

17. (Original) The method of claim 14 wherein said reactive oxygen atoms are formed by generating a plasma from O₂ molecules.

18. (Original) The method of claim 14 wherein said reactive oxygen atoms are formed by generating a plasma from N₂O molecules.

19. (Original) The method of claim 14 wherein said reactive oxygen atoms are formed by generating a plasma from O₂ molecules utilizing microwaves.

20. (Original) The method of claim 14 wherein said deposited oxide is a silicon-oxide.

21. (Original) The method of claim 14 wherein said deposited oxide is a metal-oxide.

22. (Original) The method of claim 21 wherein said deposited metal oxide is a transition metal oxide.

23. (Original) The method of claim 22 wherein said transition metal-oxide is tantalum pentaoxide (Ta_2O_5).

24. (Currently Amended) A method of forming a capacitor, said method comprising:

forming a bottom electrode;

depositing a transition metal dielectric on said bottom electrode in a deposition chamber;

generating a plasma comprising ionized oxygen atoms by forming said plasma from oxygen (O_2) gas in a microwave applicator cavity of a remote plasma generator;

flowing said ionized oxygen atoms through a conduit coupling said microwave applicator cavity and said deposition chamber, wherein said ionized oxygen atoms become electrically neutral reactive oxygen atoms before reaching said deposition chamber;

annealing said as deposited transition metal dielectric in said deposition chamber by exposing said as deposited transition metal dielectric to said electrically neutral reactive oxygen atoms to form an electrically neutral reactive oxygen atom exposed as deposited dielectric layer and to improve the electrical performance of the as deposited dielectric layer; and

forming a top electrode above said electrically neutral reactive oxygen atom exposed transition metal dielectric.

25. (Original) The method of claim 24 wherein said transition metal dielectric is tantalum pentaoxide (Ta_2O_5) deposited by chemical vapor deposition utilizing a source gas comprising TAETO.

26. (Original) The method of claim 24 wherein said transition metal dielectric is tantalum pentaoxide (Ta_2O_5) formed by chemical vapor deposition utilizing a source gas comprising TAT-DMAE.

27. (Original) The method of claim 25 wherein said tantalum pentaoxide dielectric layer is formed utilizing a source gas comprising O_2 .

28. (Original) The method of claim 24 wherein said transition metal dielectric layer is deposited at a temperature between 300-500°C.

29. (Original) The method of claim 24 wherein said transition metal dielectric is formed with a source gas comprising N_2O .

30. (Canceled)

31. (Original) The method of claim 24 wherein said transition metal dielectric film is annealed at a temperature less than 400°C.

32-45. (Withdrawn)